

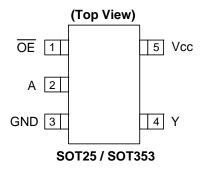
Description

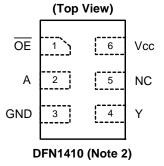
The 74LVCE1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 Exceeds 200-V Machine Model (A115-A)
 Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- · Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments





Applications

- · Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- · General Purpose Logic
- Wide array of products such as.
 - o PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Cell Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

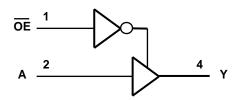
2. Pin 2 and pin 5 of the DFN1410 package are internally connected.



Pin Descriptions

Pin Name	Description				
ŌĒ	Output Enable (active low)				
Α	A Data Input				
GND	Ground				
Υ	Data Output				
Vcc	Supply Voltage				

Logic Diagram



Function Table

Inp	uts	Output			
ŌĒ	ŌE A				
L	Н	Н			
L	L	L			
Н	Х	Z			



Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	٧
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	٧
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	٧
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 4)

Symbol		Parameter	Min	Max	Unit	
\/	On a ratio a Valta as	Operating	1.4	5.5	V	
V_{CC}	Operating Voltage	Data retention only	1.2		V	
		V _{CC} = 1.4 V to 1.95 V	0.65 X V _{CC}			
\/	High lavel lagest Valtage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
V_{IH}	High-level Input Voltage	V _{CC} = 3 V to 3.6 V	2		V	
		V _{CC} = 4.5 V to 5.5 V	0.7 X V _{CC}			
		V _{CC} = 1.4 V to 1.95 V		0.35 X V _{CC}		
W	V Low lovel input veltage	V _{CC} = 2.3 V to 2.7 V		0.7	V	
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V	
		V _{CC} = 4.5 V to 5.5 V		0.3 X V _{CC}		
Vı	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{CC}	V	
	High-level output current	Vcc=1.4 V		-3		
		V _{CC} = 1.65 V		-4	0	
		V _{CC} = 2.3 V		-8		
I _{OH}		V 2V		-16	mA	
		$V_{CC} = 3 V$		-24		
		V _{CC} = 4.5 V		-32		
		Vcc=1.4 V		3		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8	mΑ	
I _{OL}	Low-level output current			16		
		$V_{CC} = 3 V$		24		
		V _{CC} = 4.5 V		32		
		V _{CC} = 1.4 to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	rate	$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5		
T _A	Operating free-air temperature		-40	85	°C	

Note: 4. Unused inputs should be held at Vcc or Ground.



Electrical Characteristics (All typical values are at Vcc = 3.3V, T_A = 25°C)

Over recommended free-air temperature range (unless otherwise noted)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit	
		$I_{OH} = -100 \mu A$	1.4 V to 5.5V	V _{CC} - 0.1				
		$I_{OH} = -3mA$	1.4 V	1.05				
		$I_{OH} = -4mA$	1.65 V	1.2				
V_{OH}	High Level Output Voltage	$I_{OH} = -8mA$	2.3V	1.9			V	
	Voltage	I _{OH} = -16mA	3 V	2.4				
		$I_{OH} = -24mA$	3 V	2.3				
		$I_{OH} = -32mA$	4.5 V	3.8				
		$I_{OL} = 100 \mu A$	1.4 V to 5.5V			0.1		
		$I_{OL} = 3mA$	1.4V			.4		
		$I_{OL} = 4mA$	1.65 V			0.45		
V_{OL}	High-level Input Voltage	$I_{OL} = 8mA$	2.3V			0.3	V	
		I _{OL} = 16mA	3 V			0.4		
		$I_{OL} = 24mA$	3 V			0.55		
		$I_{OL} = 32mA$	4.5			0.55		
I _I	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μΑ	
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 5.5V$	0			± 10	μA	
I _{OZ}	Z State Leakage Current	$V_0 = 0 \text{ to } 5.5 \text{V}$	3.6V			10	μA	
I _{CC}	Supply Current	$V_1 = 5.5V$ of GND $I_0=0$	1.4 V to 5.5V			10	μA	
Δl _{CC}	Additional Supply Current	One input at V _{CC} – 0.6 V Other inputs at V _{CC} or GND	3 V to 5.5V			500	μA	
C_{i}	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF	
	The second Decistors	SOT25	(Note 5)		204			
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5) 371			°C/W		
	CONTROL AIRDIGIT	DFN1410	(Note 5)		430			
	TI 15 : 1	SOT25	(Note 5)		52			
θ_{JC}	Thermal Resistance Junction-to-Case	SOT353	(Note 5)		143		°C/W	
	0011011011-10-0036	DFN1410	(Note 5)		190		1	

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Parameter	From	то	Vcc = ± 0			: 1.8 V .15V		: 2.5 V).2V		3.3 V 3.3V	Vcc :	= 5 V).5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	A	Υ	1.9	6.9	1.3	4.8	0.5	3.6	0.4	3	0.4	3	ns

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From																							From (Input)	_	_	то	Vcc = ± 0			: 1.8 V .15V		2.5 V 0.2V		3.3 V 3.3 V	Vcc :	= 5 V).5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	• · · · ·																									
t _{pd}	Α	Y	2.8	9	1.9	6.3	0.9	4.4	0.8	3.6	0.9	3.6	ns																									
t _{en}	OE	Υ	3.3	10.1	2.3	7	1.2	5.2	0.8	4.3	0.9	4.5																										
t _{dis}	ŌE	Y	1.3	9.2	0.9	6.4	0.8	4	0.8	4.1	0.9	3.7																										

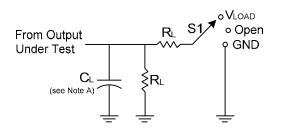
Operating Characteristics

 $T_A = 25$ °C

	Parameter			Vcc = 1.5 V	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
			Conditions	TYP	TYP	TYP	TYP	TYP	
	Power dissipation	Outputs enabled	f = 10 MHz	20	20	20	21	22	۲.
	dissipation capacitance	Outputs disabled	I = IU WIMZ	2	2	2	2	4	pF

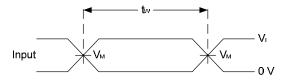


Parameter Measurement Information

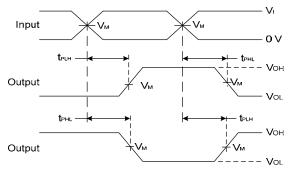


TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Vcc	In	puts	Was	C	RL
VCC	Vı	t _r /t _f	- V _M	CL	ΚL
1.5V±0.1V	V _{CC}	≤2ns	V _{CC} /2	15pF	1ΜΩ
1.8V±0.15V	V _{cc}	≤2ns	V _{CC} /2	15pF	1ΜΩ
2.5V±0.2V	V _{cc}	≤2ns	V _{CC} /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1ΜΩ



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Output
Waveform 1
S1 at V_{LOAD}
(see Note B)

Output
Waveform 2
S1 at GND
(see Note B)

Output
Waveform 2
S1 at GND
(see Note B)

Voltage Waveform Enable and Disable Times
Low and High Level Enabling

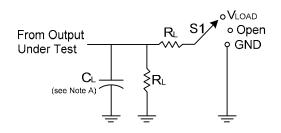
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}
- E. t_{PZL} and t_{PZH} are the same as t_{EN}
- F. t_{PLH} and t_{PHL} are the same as t_{PD}.

Figure 1. Load Circuit and Voltage Waveforms

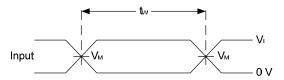


Parameter Measurement Information (Continued)

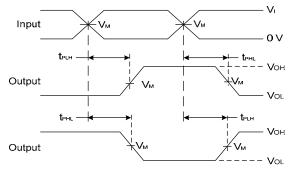


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Vcc	Inp	outs	V _M	CL	RL
	Vı	t _r /t _f	- 101	o _L	- 1,_
1.5V±0.1V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Output Control

Output Waveform 1
S1 at V_{LOAD} (see Note B)

Output Waveform 2
S1 at GND
(see Note B) V_M V_M V_M V_M $V_{LOAD}/2$ $V_{CA}/2$ $V_{CA}/2$

Voltage Waveform Enable and Disable Times Low and High Level Enabling

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
- E. t_{PZL} and t_{PZH} are the same as t_{EN0}
- F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$

Figure 2. Load Circuit and Voltage Waveforms



Ordering Information

T4LVCE1G 125 XXX - 7

Logic Device Function Package Packing

74 : Logic Prefix 125 : 3-State Buffer W5 : SOT25 7 : Tape & Reel

LVCE: 1.4 to 5.5V

OE-Low

SE: SOT353 FZ4: DFN1410

LVCE: 1.4 to 5.5V Family

1G : One gate

Dovice	Package	Packaging	7" Tape and Reel	
Device	Code	(Note 5)	Quantity	Part Number Suffix
74LVCE1G125W5-7	W6	SOT25	3000/Tape & Reel	-7
74LVCE1G125SE-7	SE	SOT353	3000/Tape & Reel	-7
74LVCE1G125FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Marking Information

(1) SOT25 and SOT353

(Top View)

5 4 XX Y W X

Part Number

74LVCE1G125W5

74LVCE1G125SE

XX: Identification code

Y: Year 0~9

SOT25

SOT353

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

PY

PΥ

52 and 53 week X : A~Z : Internal code

(2) DFN1410

(Top View)

 XX: Identification Code

Y: Year: 0~9

 $\overline{\underline{W}}$: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

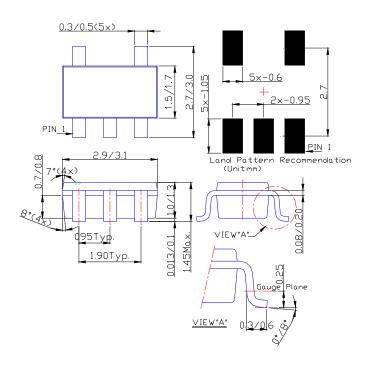
52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVCE1G125FZ4	DFN1410	PY

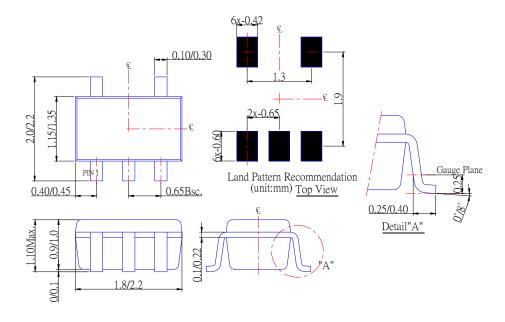


Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



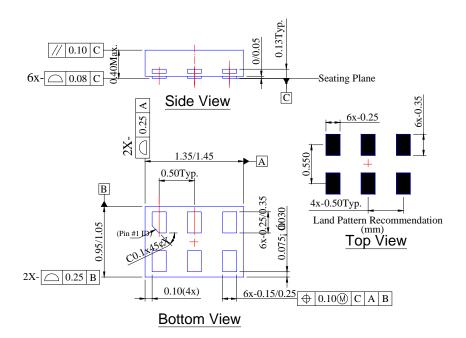
(2) Package Type: SOT353





Package Outline Dimensions (All Dimensions in mm)

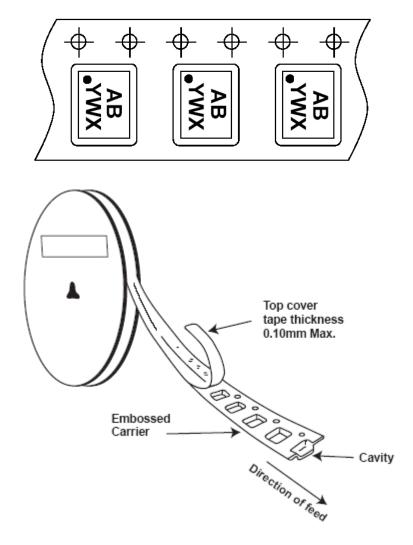
(3) Package Type: DFN1410





Taping Orientation (Note 7)

For DFN1410



Note: 7. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



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